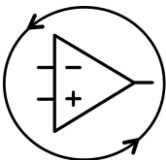


Cryogenic DAQs and FPGAs for Magnet Diagnostics

DIAGNOSTICS WORK GROUP
MEETING #4

Marcos Turqueti

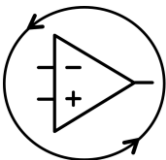
06/12/2020



LBNL Activities

ATAP, Nuclear Sciences and Engineering

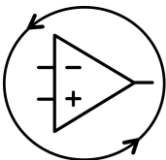
- Active Cryogenic Electronic Envelope (2013)
U.S. Patent No. 10,240,875 (Supercon)
- Commercial off-the-shelf cryogenic components (4k-77k)
ADCs, Amplifiers, Diodes, FPGAs, Laser Diodes, Optical Isolators , Voltage Regulators, Transistors and Passives
- Field Programmable Gate Array (FPGA) on Cryogenic Environments (first board 2015)
- FPGA operating with COTS ADC (LTC2418)
- FPGA based ADC
- Cryogenic Magnetic Sensors
Acoustic Sensors (Maxim)
Electron Beam Sensor (LDRD)
- 160nm Cryogenic ASIC (2018)
16 channels 12b 10MSPS ADC, 1 MSPS 10b ADC, Charge Amplifier, Voltage Regulator, Strain Gauge, Sea-of-Transistors, Memory (C.Grace, D.Gnani)
- 3th Gen FPGA Test Board (2018)
- 4th Gen FPGA/DAQ (2019-2020) – LBNL –Fermilab/CD



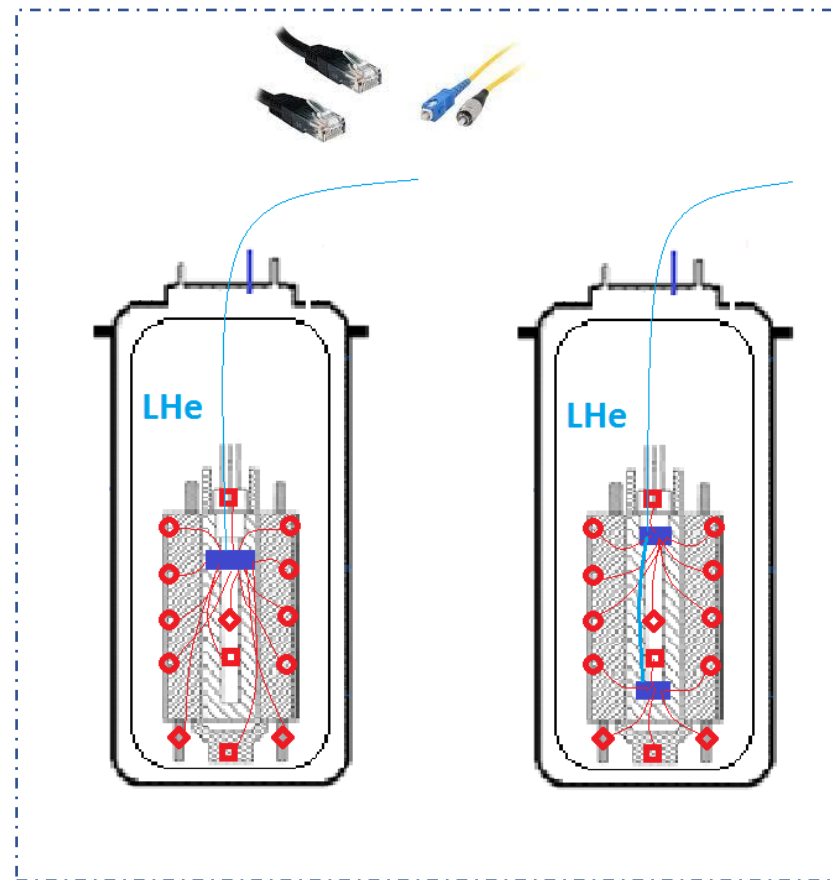
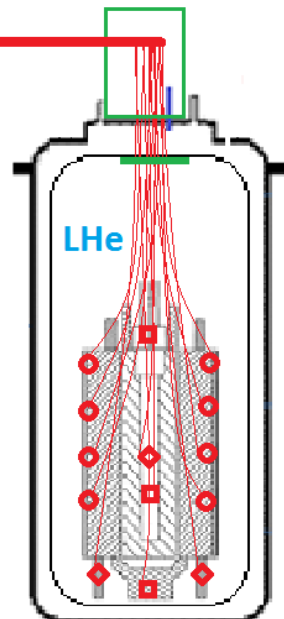
Motivation

Instrumentation of Cryogenic Experiments

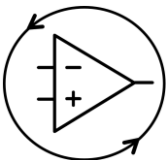
- Data interface fully digital
- Simplification of cryostat feedthrough
- Noise reduction
- System simplification (no long analog cables present)
- Flexibility
- Cost reduction
- Increase time of oxide breakdown



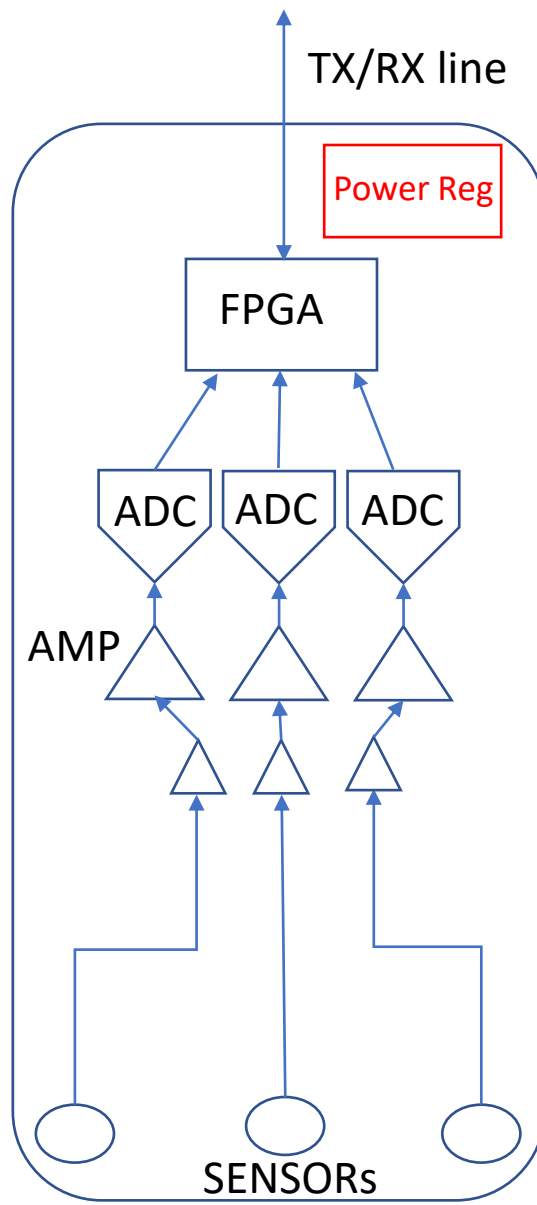
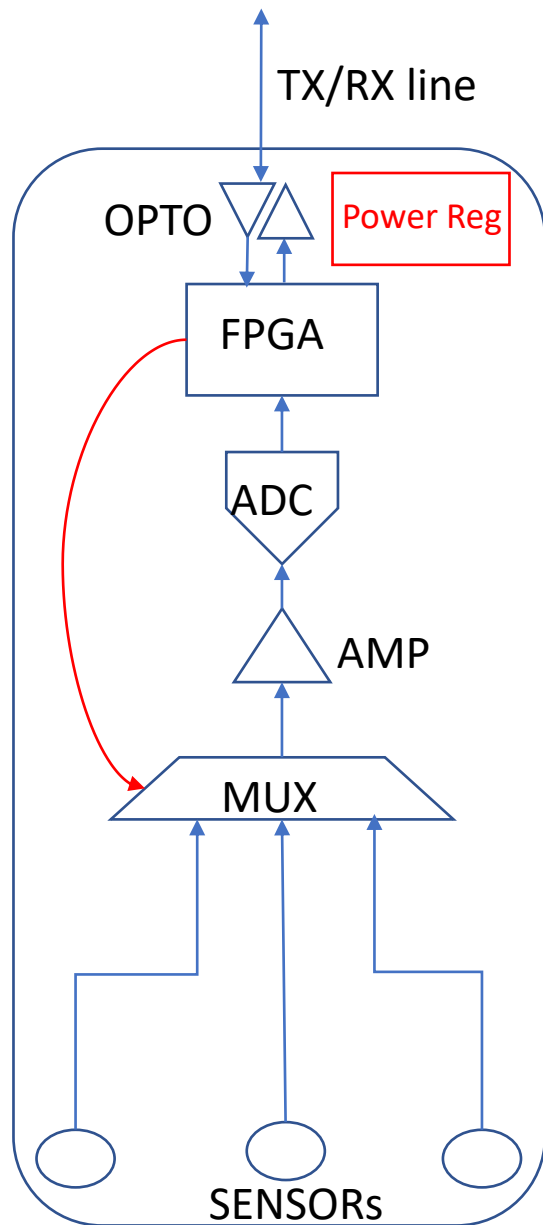
Data Acquisition for Magnet Diagnostics



- ◆ Strain Gauge
- Voltage Taps
- Temperature Sensor



Architectures for cryogenic DAQ



Power:

- Switched Capacitor+LDO
- Power over Fiber
- LED supply

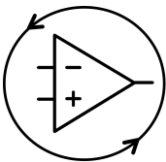
Communications:

- JESD
- LVDS
- CMOS
- Ethernet (PHY?)

Over copper or fiber
Single or multiple lanes.
Typically one lane provides 300Mbps

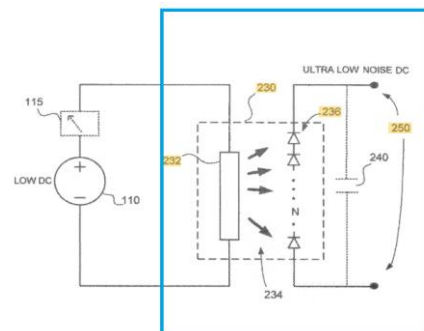
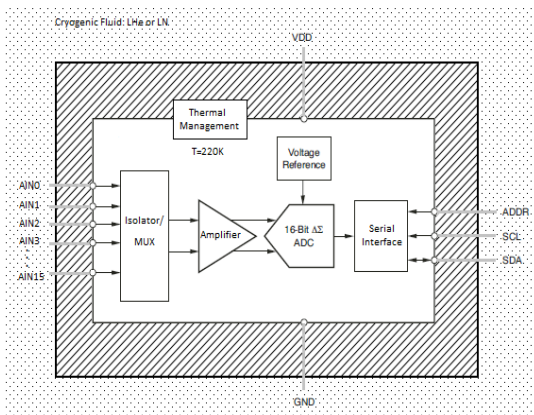
Isolation:

Opto or capacitive



Bypassing the Problem

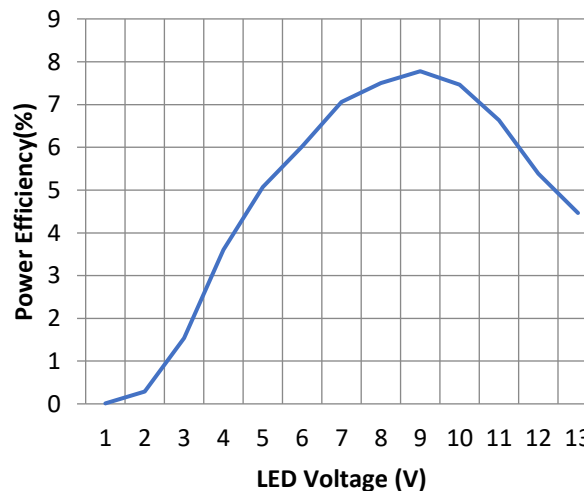
ACEe - Active Cryogenic Electronic Envelope (Gen 1)

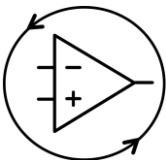


Alternative: Power Over Fiber

- For LHe Operation
- Internal Temperature (70k to 100k)
- 16 analog channels
- 3000V input multiplexed isolation
- 16 bit ADC providing 1 MSPS per channel
- Low noise ADC, SFDR >100dB
- 3 wires digital interface
- Automatic temperature control
- Internal voltage reference
- 250mW maximum power dissipation
- Non-magnetic components

Electro-Optical Power Converter
LED: AA1010SE28Zc 80nm shift at LHe



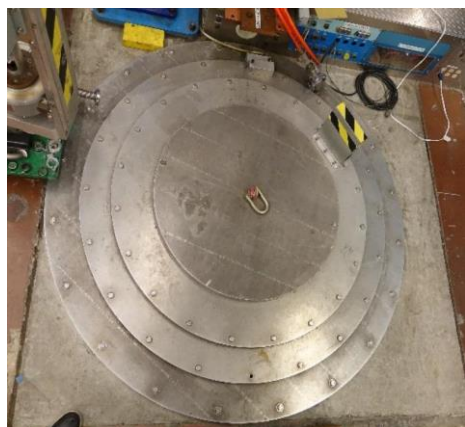


Systems with COTS cryogenic components

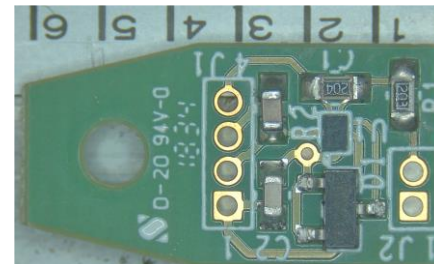
LN Test



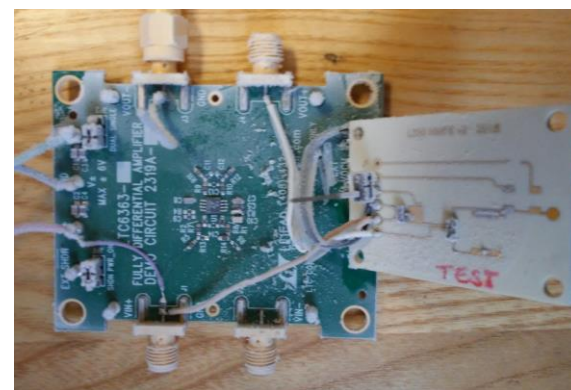
LHe Test



- **ADCs**
 - 24b / 20kSPS
 - 12b / 10MSPS
 - 4b / 500MSPS
- **Amplifiers** (up to 500MHz)
- **Diodes** (HV protection 1A)
- **FPGAs** (28nm- 45nm)
- **Laser Diodes Optical Isolators**
- **Voltage Regulators**
 - LDO and SW capacitor
- **Transistors**
 - JFET
 - HEMT
 - MOSFET
- **Passives**
 - Capacitors and resistors



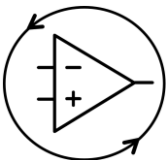
Slow Amplifier
(Acoustic Instrumentation)



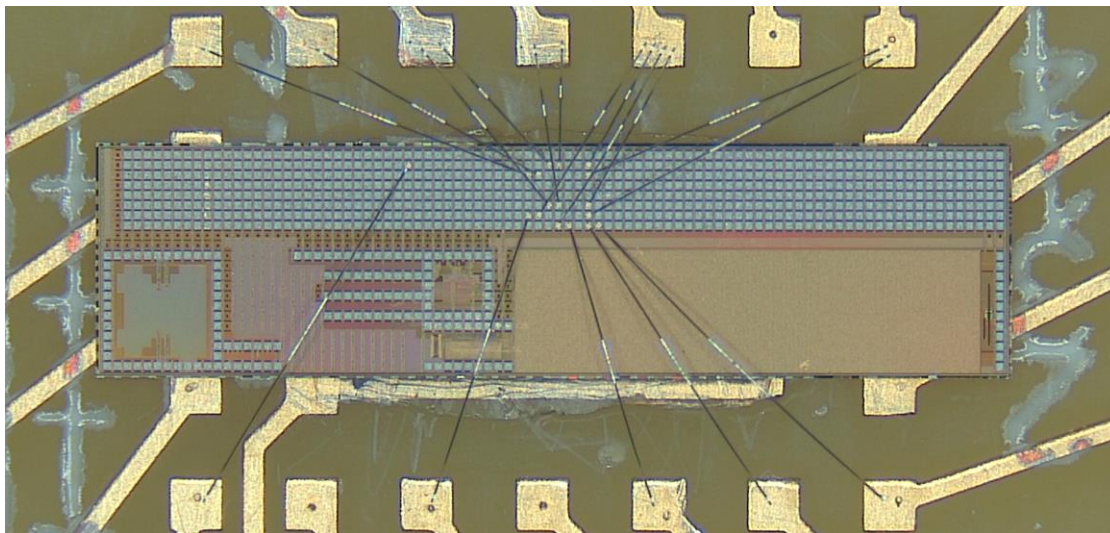
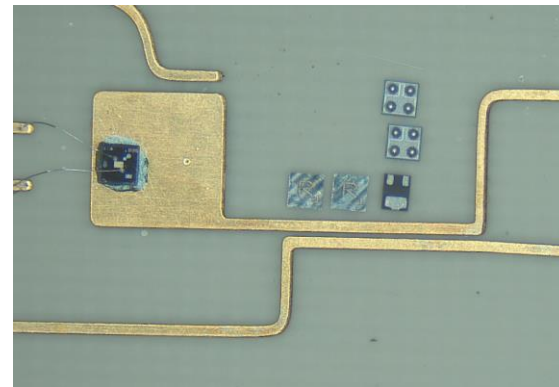
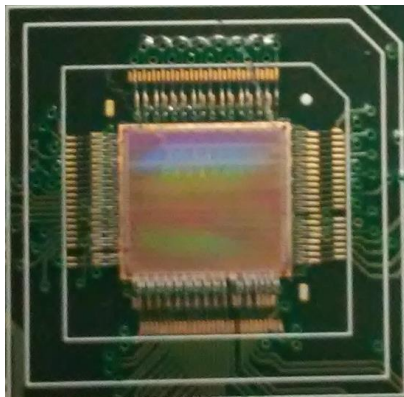
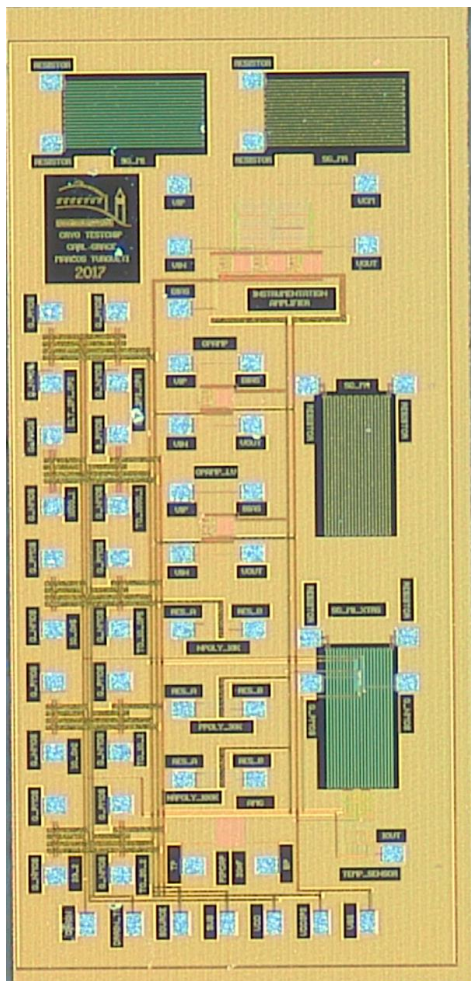
Fast Amplifier -500MHz



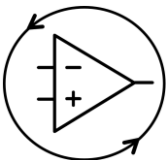
Basic COTS component



ASICs for Cryogenics

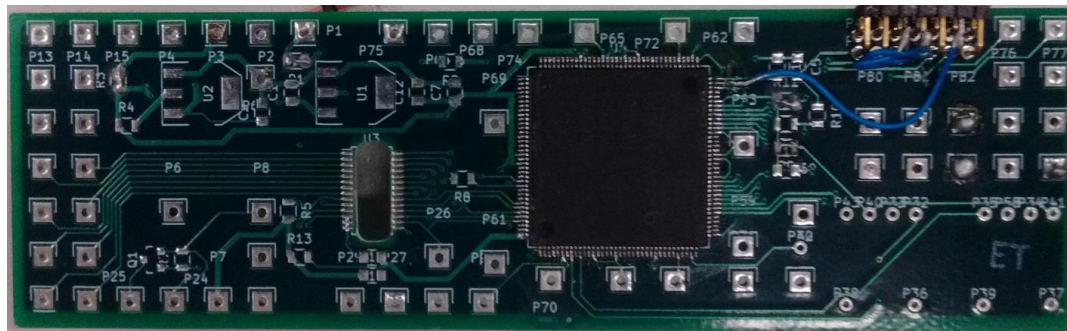


\$\$!, Development time, Not Flexible
Application Specific, Low Power

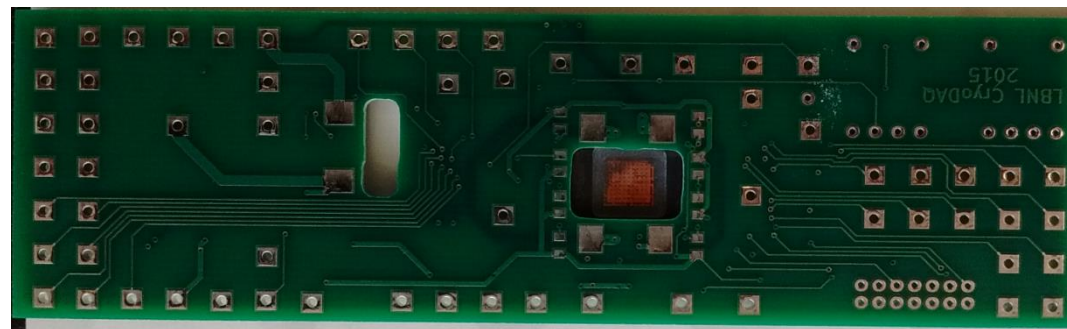


CryoDAQ

- Current versions are capable of dealing with 32 analog channels
- Data is transmitted fully digital
- System resides inside the cryostat and is capable of operating at 4.2k
- Tests were already performed with strain gauges
- Two existing versions:
 - Strain Gauge (SG) version: 20 SPS per channel
 - Voltage Taps (VT) version: 200kSPS per channel



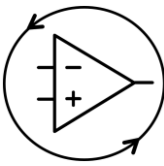
TOP



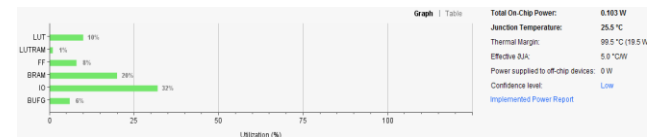
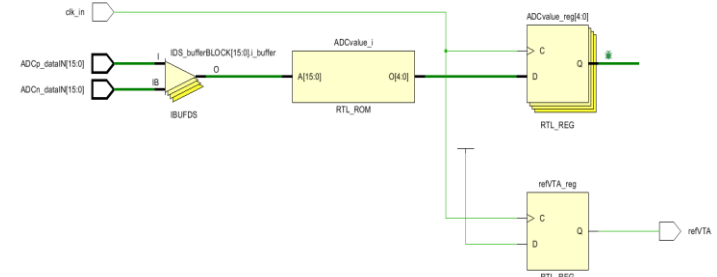
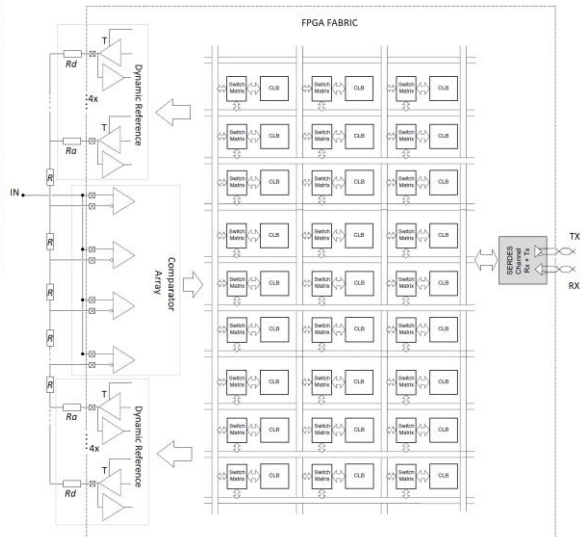
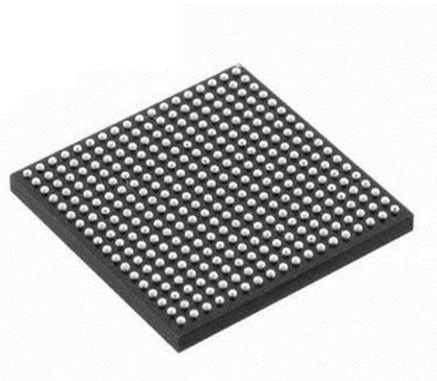
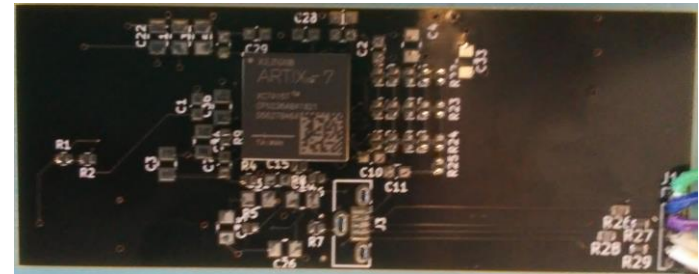
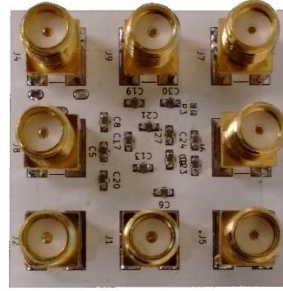
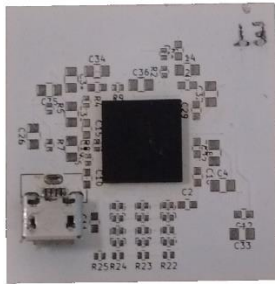
BOTTOM



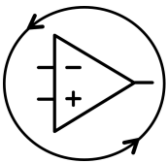
Leaded Part



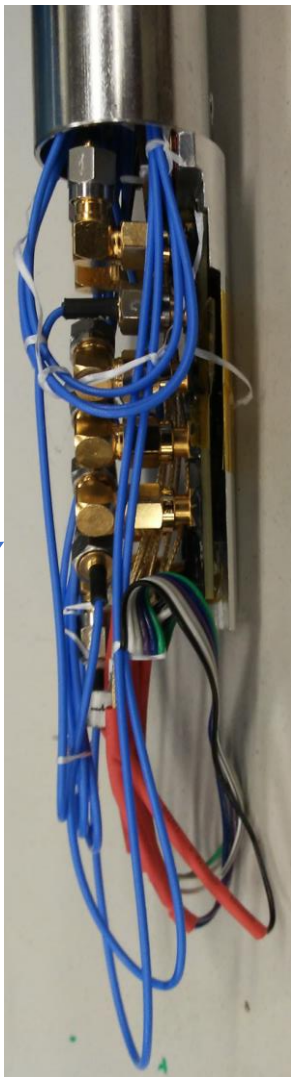
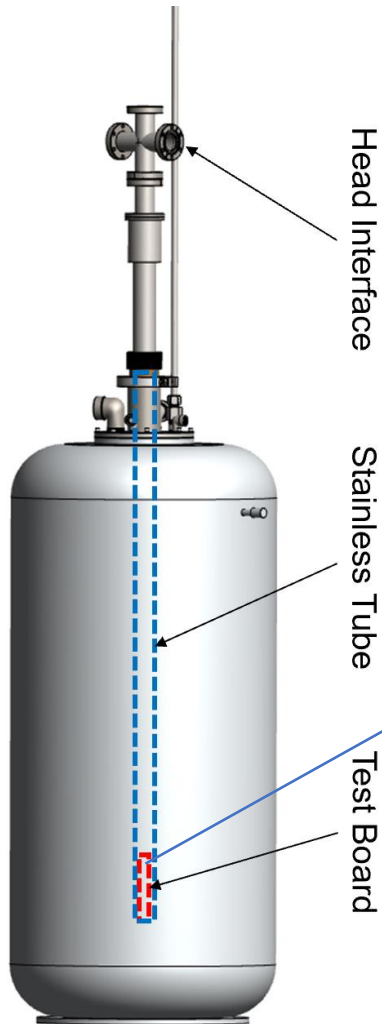
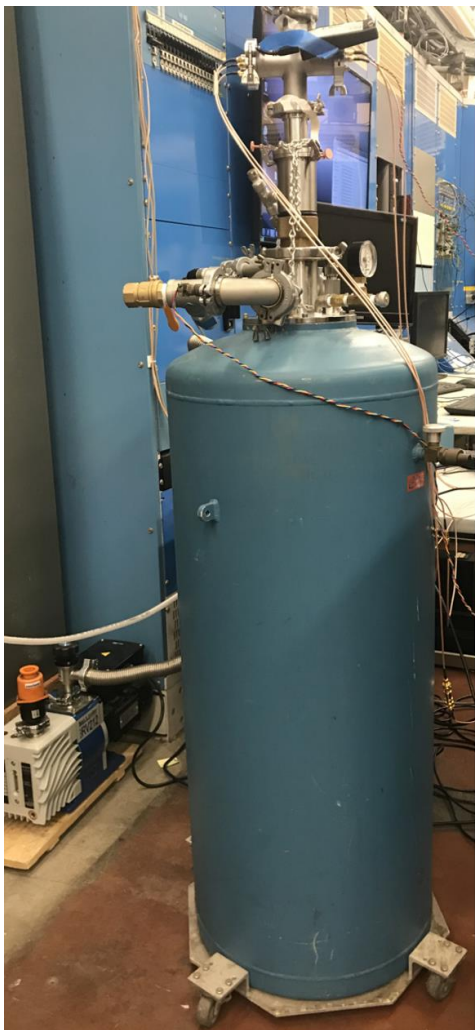
FPGA Based n-bit Analog to Digital Converter



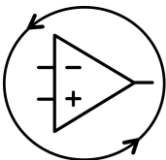
Reconfigurable Flash Folding Architecture.
With this architecture it is possible to change the ADC resolution on the fly.



Test Setup at LBNL



*Maxim +Bleximo



Threshold (V_{th})

For an n-channel enhancement mode MOS transistor, the formula for threshold voltage is

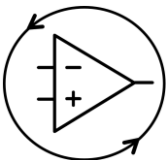
$$V_{Th} = V_{FB} + 2\phi_F + \frac{\sqrt{2\epsilon_0\epsilon_s q N_A (2\phi_F + V_{SB})}}{C_{ox}},$$

where V_{FB} = flat-band voltage, ϕ_F = bulk potential, ϵ_0 = free-space permittivity, ϵ_s = dielectric constant of silicon, q = electronic charge, N_A = acceptor doping concentration, V_{SB} = substrate bias and C_{ox} = oxide capacitance per unit area. Also,

$$V_{FB} = \phi_{ms} - \frac{Q_f}{C_{ox}} - \frac{1}{\epsilon_0\epsilon_{ox}} \int_0^{t_{ox}} \rho_{ox}(x) x dx,$$

where ϕ_{ms} is the metal–semiconductor work function, Q_f is the fixed charge in the oxide, ϵ_{ox} is the relative permittivity of silicon dioxide, $\rho_{ox}(x)$ is the charge density in an oxide of thickness t_{ox} varying with distance x in the oxide. For an n-type polysilicon gate (STMicroelectronics 2006)

$$\phi_{ms} = -\left(\frac{k_B T}{q}\right) \ln \left(\frac{N_{D(g)} N_A}{n_i^2} \right),$$



Threshold Voltage

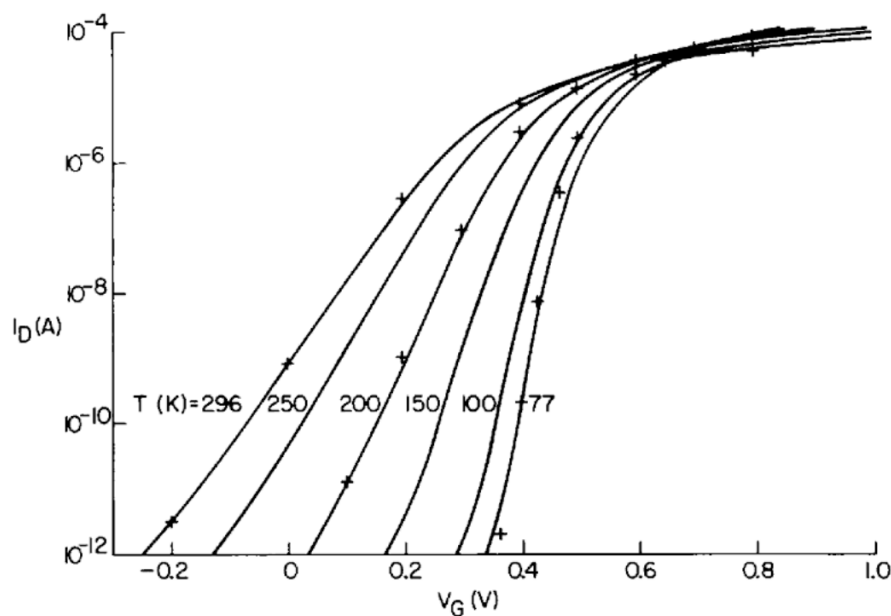
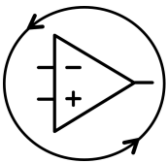
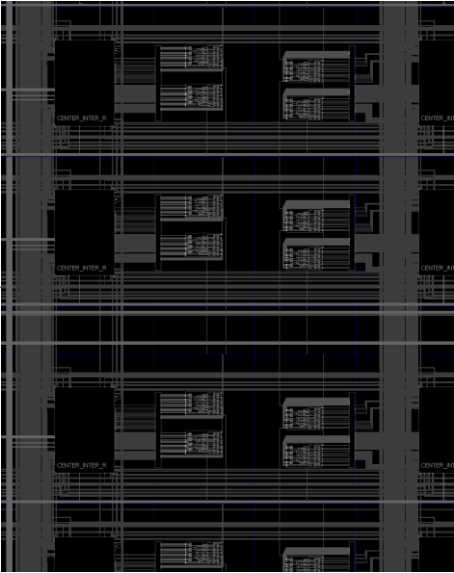
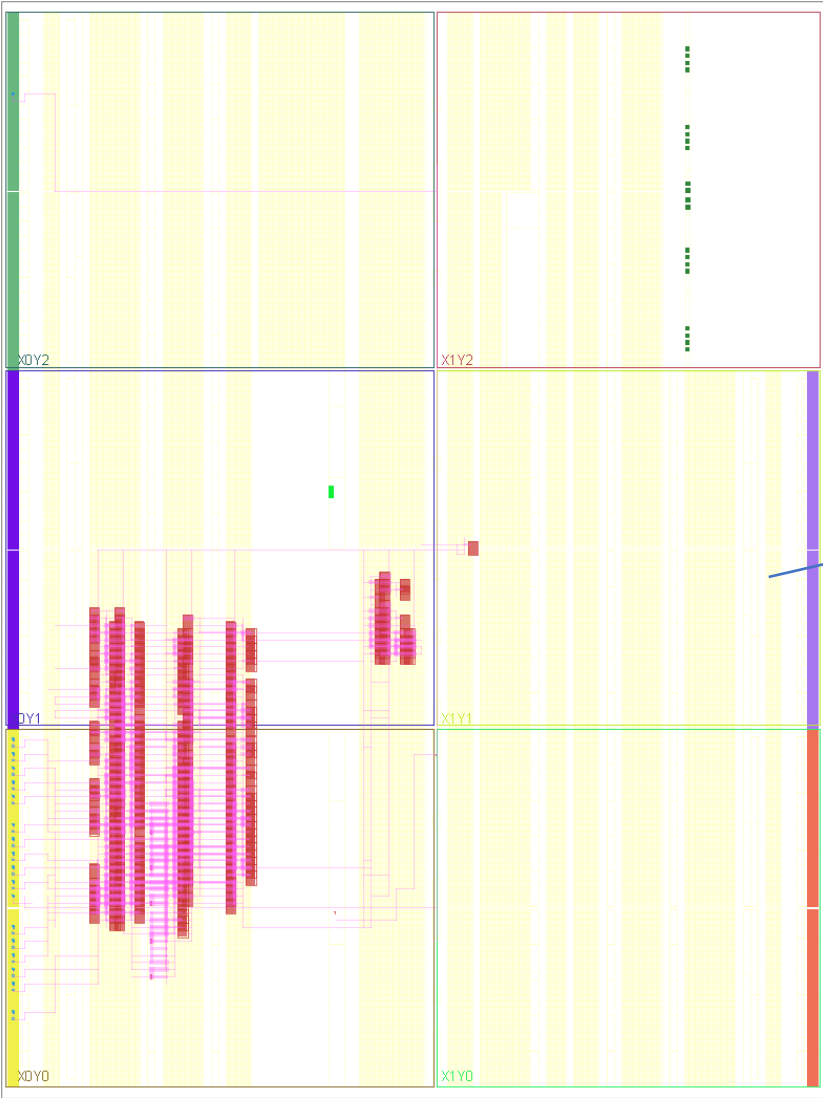


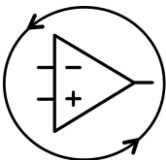
Fig. 16. Subthreshold current of **MOSFET** as a function of **temperature** from 77 to 296 K. (After **Gaensslen *et al.*** [43].) (Parameters: $L = 9 \mu\text{m}$; $W = 87 \mu\text{m}$; $V_d = 0.1 \text{ V}$; $V_{s-\text{sub}} = 0 \text{ V}$. Values, calculated by using two-dimensional model: +. Slope $= (q/2.3 kT)[C_{\text{ox}}/(C_{\text{ox}} + C_{\text{Si}} + C_{\text{FS}})]$.)



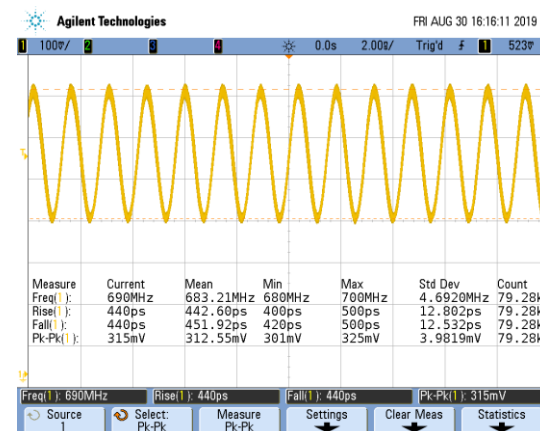
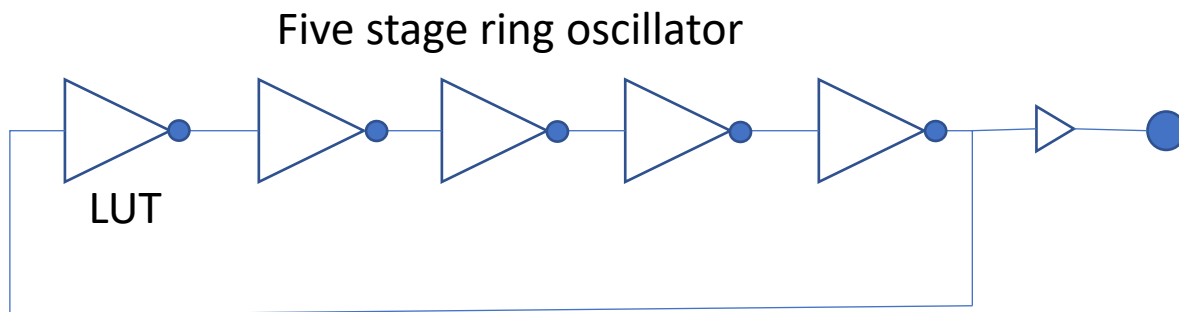
Artix 7 – FPGA (~1x1 cm)

XC7A15T





Test Circuits

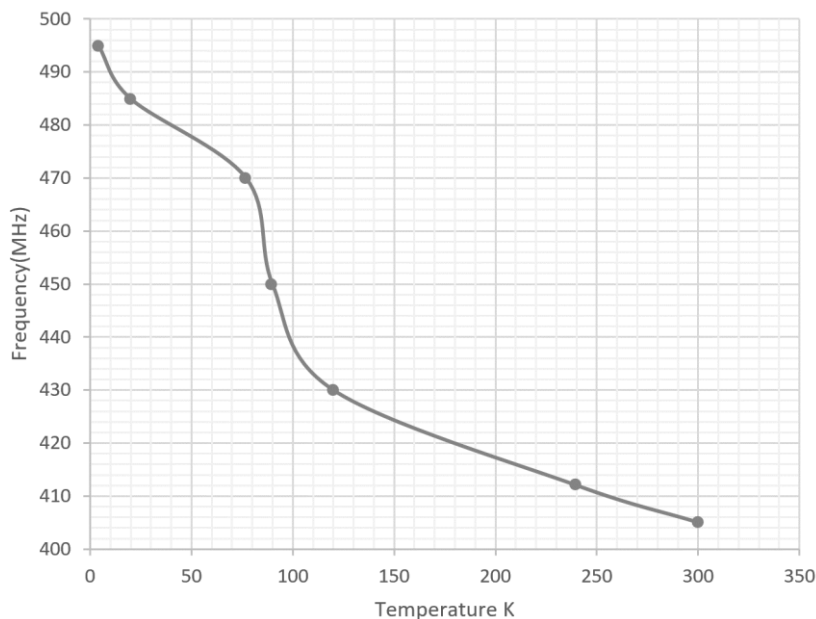


$V_{CCint} = 2.1V$

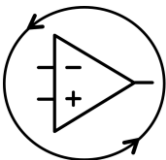
$V_{CCO} = 2.8V$

$V_{CCAUX} = 2.8V$

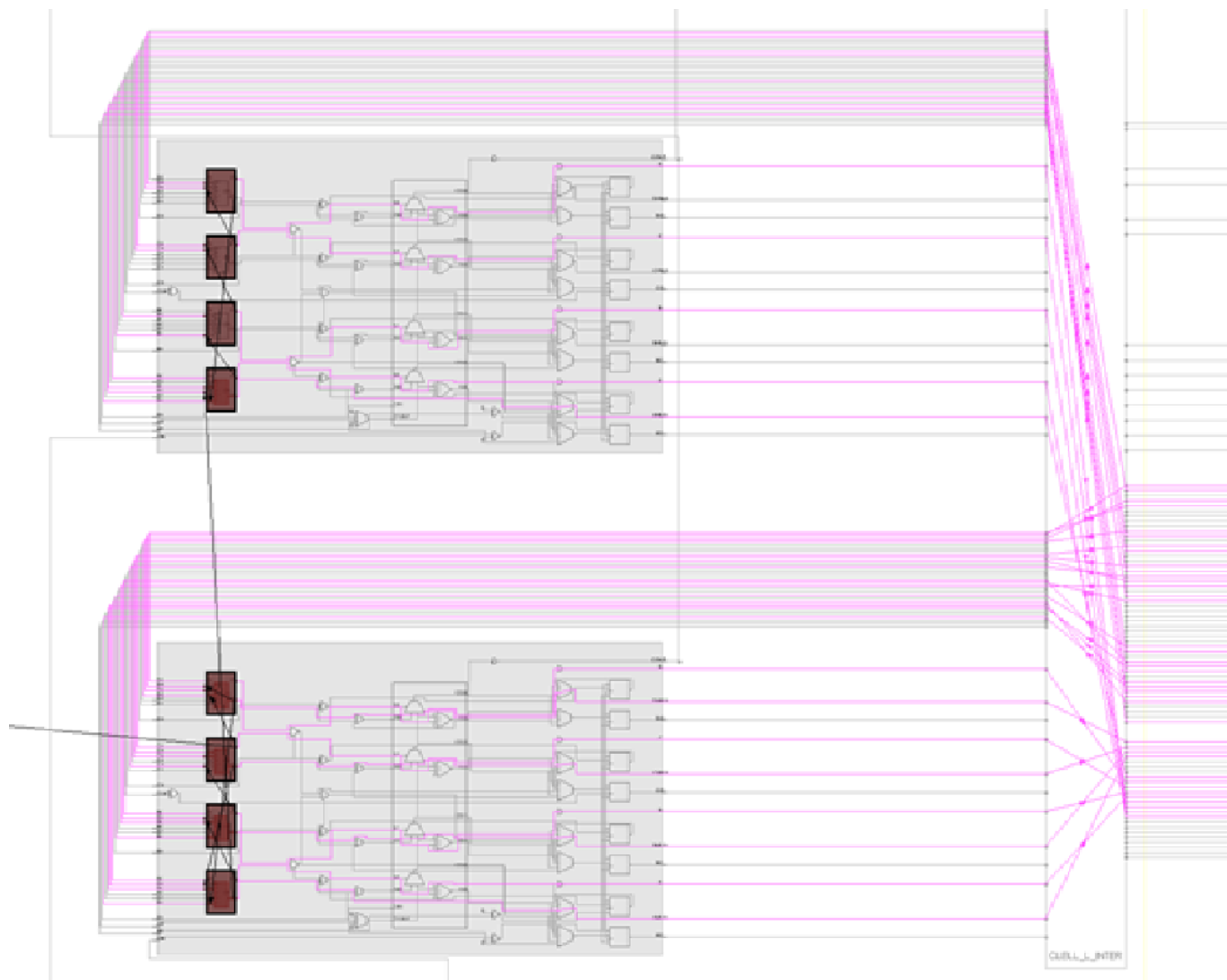
Frequency increase with temperature. Parasitic capacitance decreases

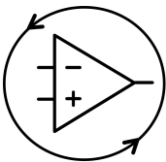


Frequency of the ring oscillator with five stages at different temperatures.



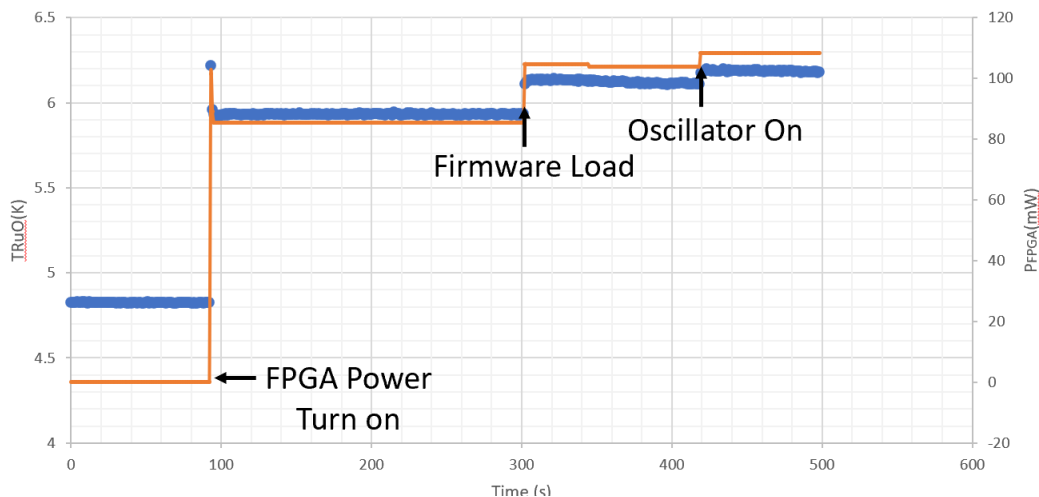
Artix 7 – Seven stages ring oscillator



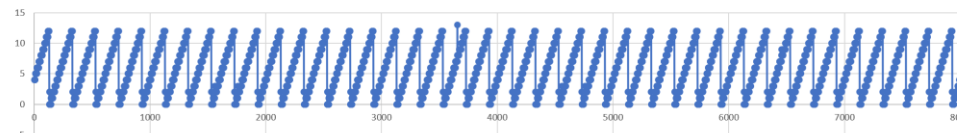
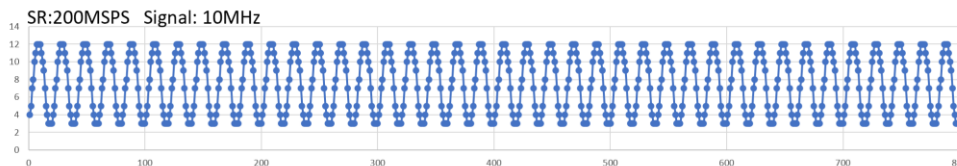
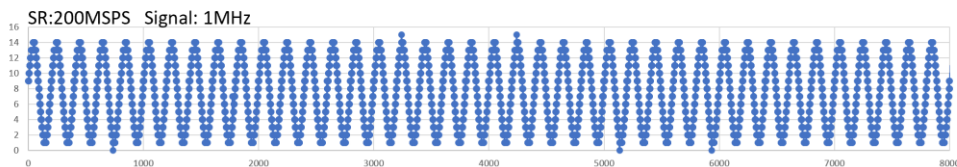


FPGA Performance Highlights

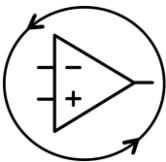
Ring Oscillator @ 800MHz
RuO Thermometer vs FPGA Power



4bADC FPGAflash ~7K

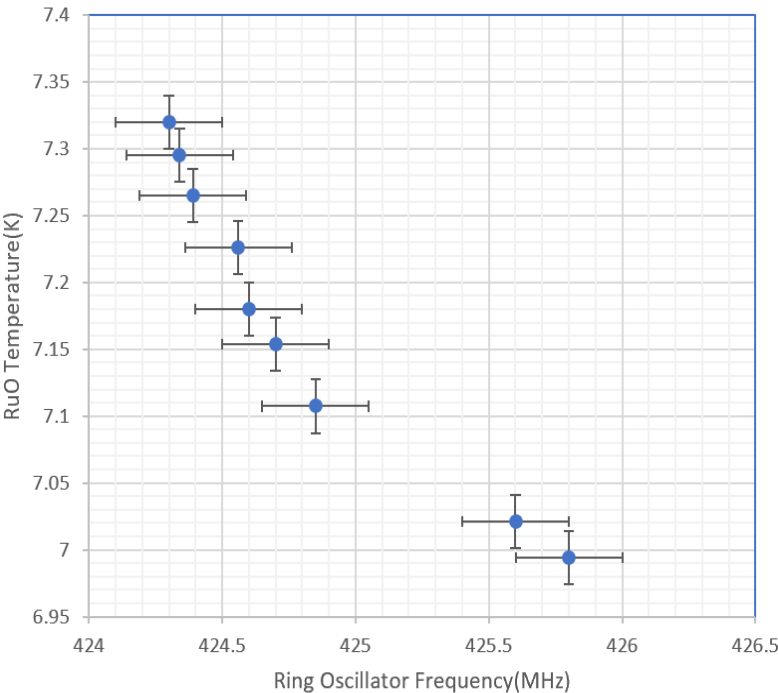


Code error here. Still calculating code error rate. Design not optimize to minimize code error.

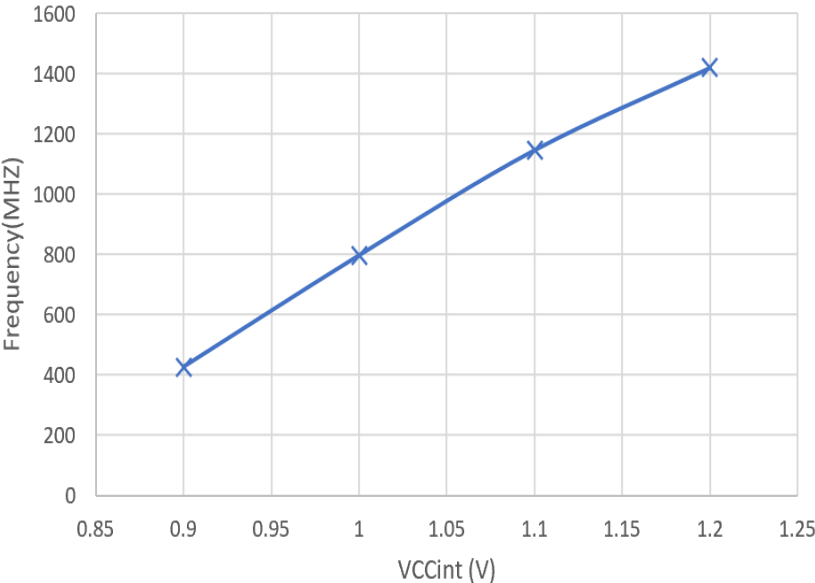


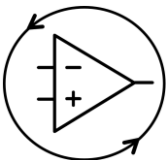
FPGA Performance Highlights

Ring Oscillator Temperature vs Frequency



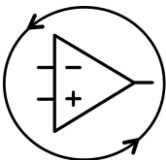
Ring Oscillator Frequency versus VCCint at 7K



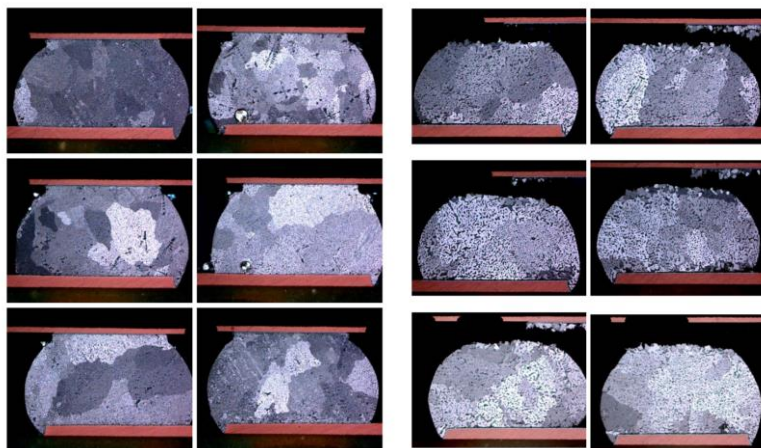
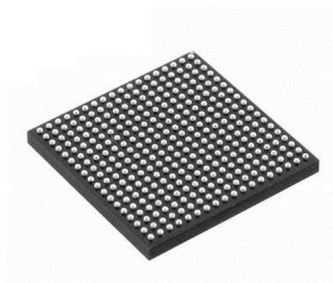


FPGA Performance Highlights

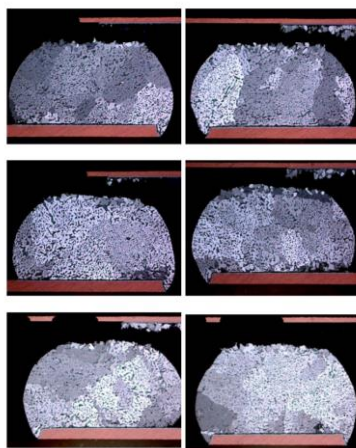
- Operates at 4.2K reliably both in Liquid Helium and on cold finger (at $\sim 4.2\text{K}$). Over 28 thermal cycles and 700 hours cold ($\sim 4\text{K}$). No degradation detected. Even when submitted to thermal shock (dipping in LN);
- 60 mW power consumption with 3 stage ring oscillator +XADC running at 400MHz;
- 150 mW power consumption with 3 stage ring oscillator +XADC running at 1000MHz;
- 550 mW power consumption with 3 stage ring oscillator +XADC running at 1400MHz (max achieved clock) LVCMOS 1.8;
- Most of the power (80% for the 1.4GHz) is dissipated at the IO driver with 50 Ohms termination, temperature at the FPGA went up to 10K;
- For the 4bit ADC at 200MSPS power consumption was 300mW with Chipscope in. Estimated to be around 140 mW without Chipscope;



BGA Reliability

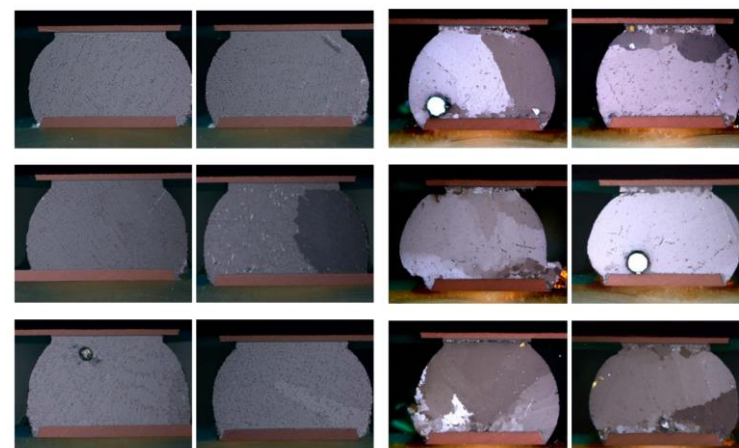


Cross-polarized images of 256 I/O reballed SnPb BGA Assemblies (as-received)

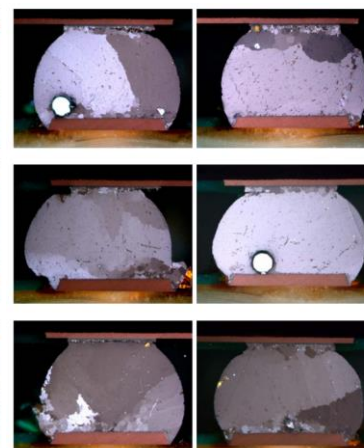


Cross-polarized images of 256 I/O reballed SnPb BGA Assemblies (after TC test)

Sn/Pb



Cross-polarized images of 256 I/O mixed BGA Assemblies (as-received)

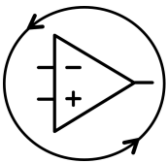


Cross-polarized images of 256 I/O lead-free BGA Assemblies (after TC test)

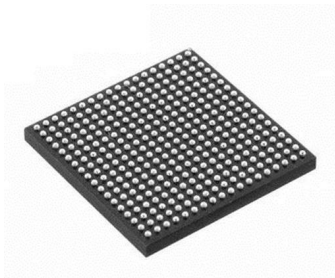
Lead Free

*TEMPERATURE CYCLING RELIABILITY OF
REBALLED AND REWORKED BALL GRID ARRAY
PACKAGES IN SNPb AND SAC ASSEMBLY Lei
Nie, Doctor of Philosophy (Ph.D.), 2010

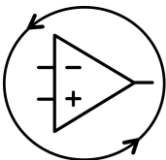
*Indium balls are even better



BGA Reliability



Cycle Type	Number of Cycles	Typical Cooldown Time(s)	Typical Warmup Time(s)	Total Number of Hours Cold(Hs)
LN Submersion	14	5	300	~5
LHe Submersion	6	7000	200000	~360
LHe Cold Finger (290K to 4.2K)	8	3000	170000	~400



Artix 7 Series

Artix-7 FPGA Product Table

COMPARE

Reset

XC7A12T

XC7A15T

XC7A25T

XC7A35T

XC7A50T

XC7A75T

XC7A100T

XC7A200T

	XC7A12T	XC7A15T	XC7A25T	XC7A35T	XC7A50T	XC7A75T	XC7A100T	XC7A200T
Logic Cells	12,800	16,640	23,360	33,280	52,160			
DSP Slices	40	45	80	90	120			
Memory (kb)	720	900	1,620	1,800	2,700			
GTP 6.6Gb/s Transceivers	2	4	4	4	4			
I/O Pins	150	250	150	250	250			

Artix-7 FPGA Product Table

COMPARE

Reset

XC7A12T

XC7A15T

XC7A25T

XC7A35T

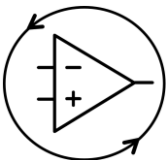
XC7A50T

XC7A75T

XC7A100T

XC7A200T

	XC7A35T	XC7A50T	XC7A75T	XC7A100T	XC7A200T
Logic Cells	33,280	52,160	75,520	101,440	215,360
DSP Slices	90	120	180	240	740
Memory (kb)	1,800	2,700	3,780	4,860	13,140
GTP 6.6Gb/s Transceivers	4	4	8	8	16
I/O Pins	250	250	300	300	500

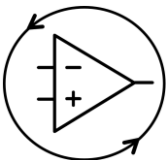


Implemented test structures

- LUT
- I/O (LVCMOS25 operating at 2.8V, 4mA)
- Ring Oscillator
- Counters (8/16 bits)
- Shift register (16 bits)
- LVDS tx/rx communications
- ADC

Evaluated at 290K, 77K*, 4.2K*

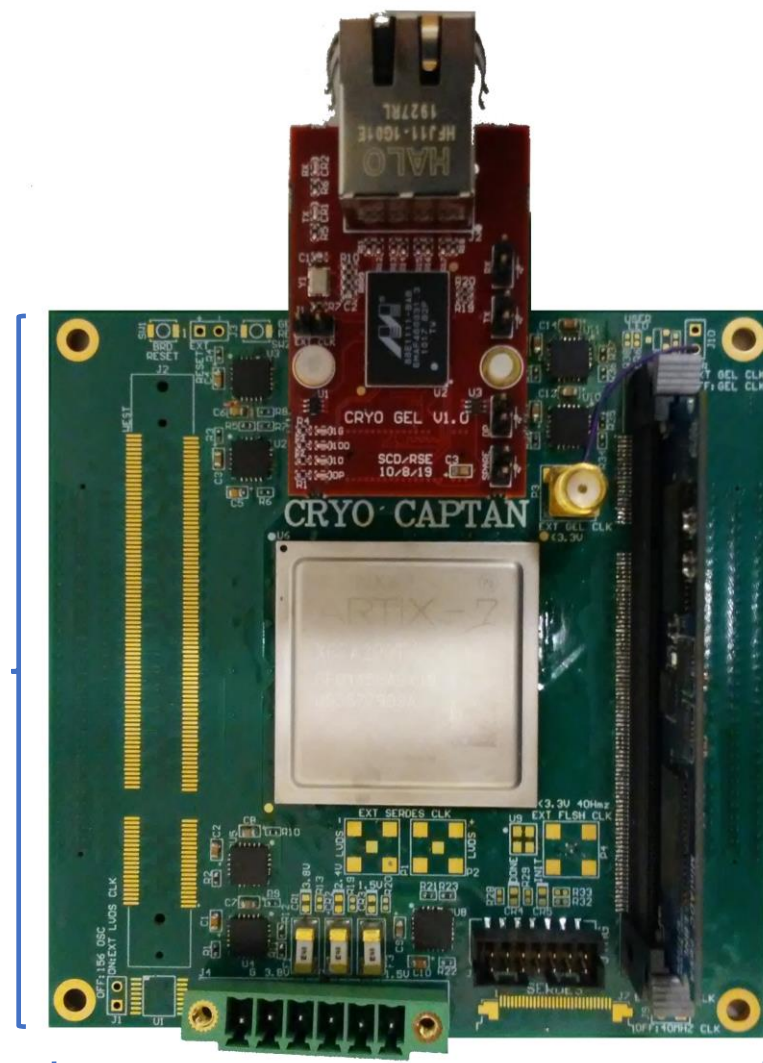
*immersed



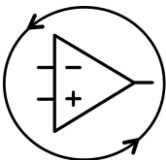
Gen4 CryoDAQ – LBNL-Fermilab

- Large Artix FPGA (28nm)
- 64 Analog channels
- External Clock
- Laser Driver for communications
- LDO's
- External Clock
- Max operational clock 1GHz
- Expected around 1 W of power dissipation

3.75"

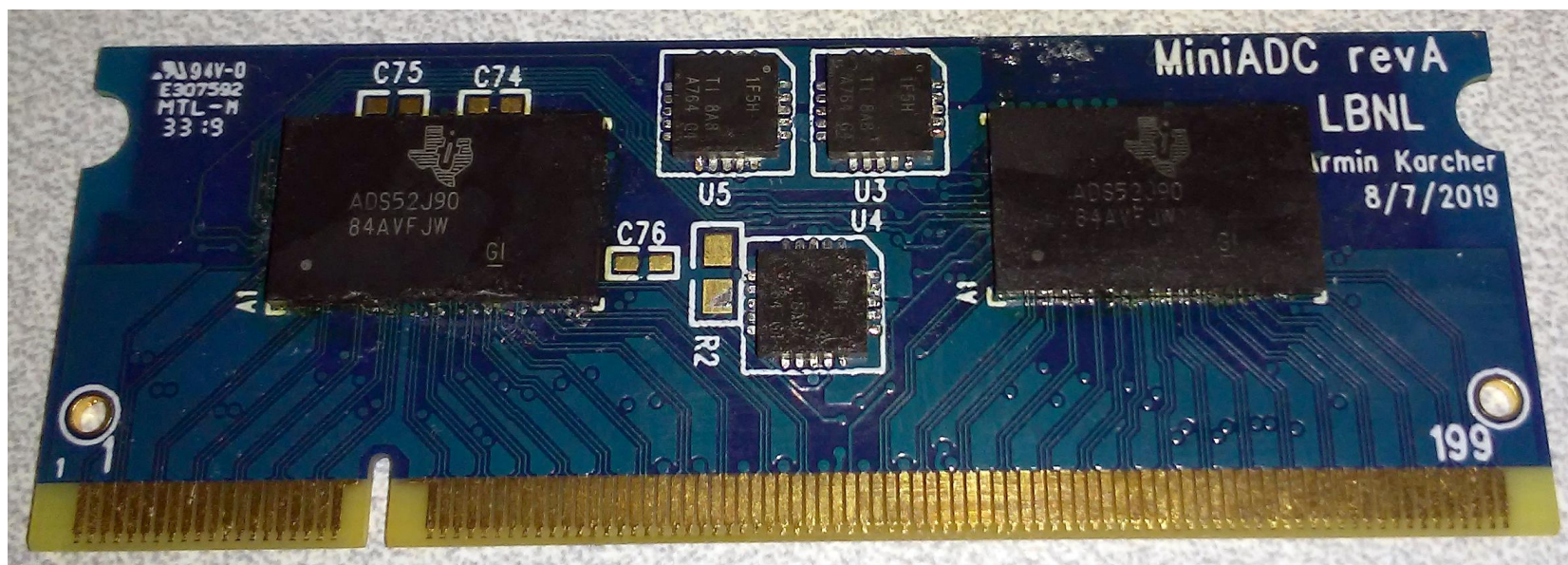


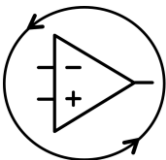
3.75"



ADC board

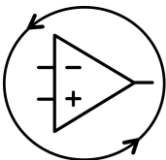
- 32 ADCs
- Sampling rate up to 100MSPS (50MHz signals)
- 14bits
- Not tested cold yet





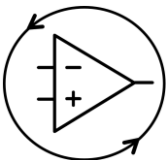
Possible Issues

- PLL, SERDES, iDelay, XADC (dedicated hardware)
- Asynchronous circuits timing uncertainty
- I/O threshold fluctuation
- Increased power consumption (+40% from room temp at 4.2K)
- Bump bond detachment with thermal cycles
- Difficult access (inside the cryostat)
- Power consumption



Conclusions

- Many options available for cryogenic data acquisition
- COTS components can be used
- Growing number of Applications Specific Integrated Circuits (ASICs) available
- Software developed needed
- More collaboration needed between potential users



To ADD

- Digital Magnet
- Ethernet PHY
- Materials SiGe, GaN ...
- Bump bond (Indium)
- Simulations/Characterization